



Welcome to [E-XFL.COM](https://www.e-xfl.com)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	56
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 27x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-FQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk22fn1m0vlk12r

Ordering Information ¹

Part Number	Memory		Maximum number of I/O's
	Flash (KB)	SRAM (KB)	
MK22FX512VLK12	512 KB	128	52
MK22FN1M0VLK12	1 MB	128	52

1. To confirm current availability of orderable part numbers, go to <http://www.freescale.com> and perform a part number search.

Related Resources

Type	Description	Resource
Selector Guide	The Freescale Solution Advisor is a web-based tool that features interactive application wizards and a dynamic product selector.	Solution Advisor
Product Brief	The Product Brief contains concise overview/summary information to enable quick evaluation of a device for design suitability.	K20PB ¹
Reference Manual	The Reference Manual contains a comprehensive description of the structure and function (operation) of a device.	K22P80M50SF5RM ¹
Data Sheet	The Data Sheet includes electrical characteristics and signal connections.	K22P80M50SF5 ¹
Package drawing	Package dimensions are provided in package drawings.	<ul style="list-style-type: none"> • QFP 80-pin: 98ASS23174W¹

1. To find the associated resource, go to <http://www.freescale.com> and perform a search using this term.

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	<ul style="list-style-type: none"> @ 70°C @ 105°C 	—	30	112	μA	
I _{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V <ul style="list-style-type: none"> @ -40 to 25°C @ 70°C @ 105°C 	—	1.25	2.1	μA	
		—	6.5	18.5	μA	
		—	37	108	μA	
I _{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit enabled <ul style="list-style-type: none"> @ -40 to 25°C @ 70°C @ 105°C 	—	0.745	1.65	μA	
		—	6.03	18	μA	
		—	37	108	μA	
I _{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit disabled <ul style="list-style-type: none"> @ -40 to 25°C @ 70°C @ 105°C 	—	0.268	1.25	μA	
		—	3.7	15	μA	
		—	22.9	95	μA	
I _{DD_VBAT}	Average current with RTC and 32kHz disabled at 3.0 V <ul style="list-style-type: none"> @ -40 to 25°C @ 70°C @ 105°C 	—	0.19	0.22	μA	
		—	0.49	0.64	μA	
		—	2.2	3.2	μA	
I _{DD_VBAT}	Average current when CPU is not accessing RTC registers <ul style="list-style-type: none"> @ 1.8V <ul style="list-style-type: none"> @ -40 to 25°C @ 70°C @ 105°C @ 3.0V <ul style="list-style-type: none"> @ -40 to 25°C @ 70°C @ 105°C 	—	0.68	0.8	μA	9
		—	1.2	1.56	μA	
		—	3.6	5.3	μA	
		—	0.81	0.96	μA	
		—	1.45	1.89	μA	
		—	4.3	6.33	μA	

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
2. 120 MHz core and system clock, 60 MHz bus 40 Mhz and FlexBus clock, and 24 MHz flash clock. MCG configured for PEE mode. All peripheral clocks disabled.
3. 120 MHz core and system clock, 60 MHz bus and FlexBus clock, and 24 MHz flash clock. MCG configured for PEE mode. All peripheral clocks enabled.
4. Max values are measured with CPU executing DSP instructions.

The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

2. $V_{DD} = 3.3\text{ V}$, $T_A = 25\text{ °C}$, $f_{OSC} = 12\text{ MHz}$ (crystal), $f_{SYS} = 96\text{ MHz}$, $f_{BUS} = 48\text{ MHz}$
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

2.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for “EMC design.”

2.2.8 Capacitance attributes

Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

2.3 Switching specifications

2.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
Normal run mode					
f_{SYS}	System and core clock	—	120	MHz	
f_{SYS_USB}	System and core clock when Full Speed USB in operation	20	—	MHz	
f_{BUS}	Bus clock	—	60	MHz	
FB_CLK	FlexBus clock	—	50	MHz	
f_{FLASH}	Flash clock	—	25	MHz	
f_{LPTMR}	LPTMR clock	—	25	MHz	
VLPR mode ¹					
f_{SYS}	System and core clock	—	4	MHz	
f_{BUS}	Bus clock	—	4	MHz	

Table continues on the next page...

Table 10. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	<ul style="list-style-type: none"> • $1.71 \leq V_{DD} \leq 2.7V$ • $2.7 \leq V_{DD} \leq 3.6V$ 	—	12	ns	
	<ul style="list-style-type: none"> • Slew enabled • $1.71 \leq V_{DD} \leq 2.7V$ • $2.7 \leq V_{DD} \leq 3.6V$ 	—	6	ns	
		—	36	ns	
		—	24	ns	

1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop, VLPS, LLS, and VLLSx modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.
2. The greater synchronous and asynchronous timing must be met.
3. This is the minimum pulse width that is guaranteed to be recognized as a pin interrupt request in Stop, VLPS, LLS, and VLLSx modes.
4. 75 pF load
5. 15 pF load

2.4 Thermal specifications

2.4.1 Thermal operating requirements

Table 11. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	-40	125	°C
T_A	Ambient temperature	-40	105	°C

2.4.2 Thermal attributes

Board type	Symbol	Description	80 LQFP	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	50	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	35	°C/W	1

Table continues on the next page...

3.1 Core modules

3.1.1 Debug trace timing specifications

Table 12. Debug trace operating behaviors

Symbol	Description	Min.	Max.	Unit
T_{cyc}	Clock period	Frequency dependent (limited to 50 MHz)		MHz
T_{wl}	Low pulse width	2	—	ns
T_{wh}	High pulse width	2	—	ns
T_r	Clock and data rise time	—	3	ns
T_f	Clock and data fall time	—	3	ns
T_s	Data setup	3	—	ns
T_h	Data hold	2	—	ns

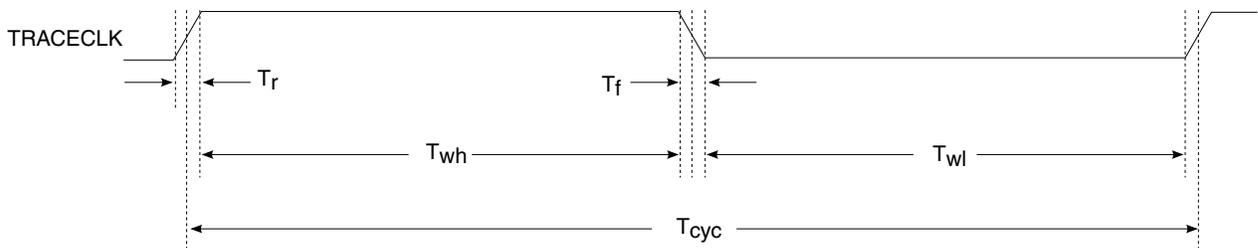


Figure 5. TRACE_CLKOUT specifications

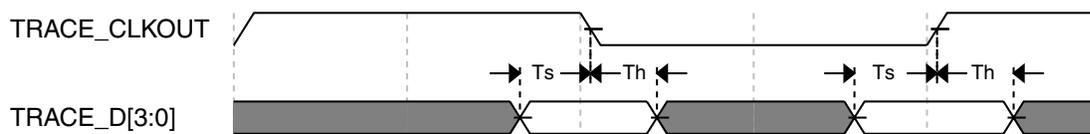


Figure 6. Trace data specifications

3.1.2 JTAG electricals

Table 13. JTAG limited voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
J1	TCLK frequency of operation			MHz

Table continues on the next page...

Table 13. JTAG limited voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
	<ul style="list-style-type: none"> Boundary Scan JTAG and CJTAG Serial Wire Debug 	0	10	
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width			
	<ul style="list-style-type: none"> Boundary Scan JTAG and CJTAG Serial Wire Debug 	50	—	ns
		20	—	ns
		10	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	2.6	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1	—	ns
J11	TCLK low to TDO data valid	—	17	ns
J12	TCLK low to TDO high-Z	—	17	ns
J13	TRST assert time	100	—	ns
J14	TRST setup time (negation) to TCLK high	8	—	ns

Table 14. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	TCLK frequency of operation			MHz
	<ul style="list-style-type: none"> Boundary Scan JTAG and CJTAG Serial Wire Debug 	0	10	
		0	20	
		0	40	
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width			
	<ul style="list-style-type: none"> Boundary Scan JTAG and CJTAG Serial Wire Debug 	50	—	ns
		25	—	ns
		12.5	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns

Table continues on the next page...

Table 16. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
		—	0	—	kΩ	
V_{pp}^5	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

- $V_{DD}=3.3$ V, Temperature =25 °C, Internal capacitance = 20 pf
- See crystal or resonator manufacturer's recommendation
- C_x, C_y can be provided by using either the integrated capacitors or by using external components.
- When low power mode is selected, R_f is integrated and must not be attached externally.
- The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

3.3.2.2 Oscillator frequency specifications

Table 17. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low-frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
$f_{osc_hi_1}$	Oscillator crystal or resonator frequency — high-frequency mode (low range) (MCG_C2[RANGE]=01)	3	—	8	MHz	
$f_{osc_hi_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	50	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

- Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.

3.4.1.5 Write endurance to FlexRAM for EEPROM

When the FlexNVM partition code is not set to full data flash, the EEPROM data set size can be set to any of several non-zero values.

The bytes not assigned to data flash via the FlexNVM partition code are used by the FTFE to obtain an effective endurance increase for the EEPROM data. The built-in EEPROM record management system raises the number of program/erase cycles that can be attained prior to device wear-out by cycling the EEPROM data through a larger EEPROM NVM storage space.

While different partitions of the FlexNVM are available, the intention is that a single choice for the FlexNVM partition code and EEPROM data set size is used throughout the entire lifetime of a given application. The EEPROM endurance equation and graph shown below assume that only one configuration is ever used.

$$\text{Writes_subsystem} = \frac{\text{EEPROM} - 2 \times \text{EESPLIT} \times \text{EESIZE}}{\text{EESPLIT} \times \text{EESIZE}} \times \text{Write_efficiency} \times n_{\text{nvmcycee}}$$

where

- Writes_subsystem — minimum number of writes to each FlexRAM location for subsystem (each subsystem can have different endurance)
- EEPROM — allocated FlexNVM for each EEPROM subsystem based on DEPART; entered with the Program Partition command
- EESPLIT — FlexRAM split factor for subsystem; entered with the Program Partition command
- EESIZE — allocated FlexRAM based on DEPART; entered with the Program Partition command
- Write_efficiency —
 - 0.25 for 8-bit writes to FlexRAM
 - 0.50 for 16-bit or 32-bit writes to FlexRAM
- n_{nvmcycee} — EEPROM-backup cycling endurance

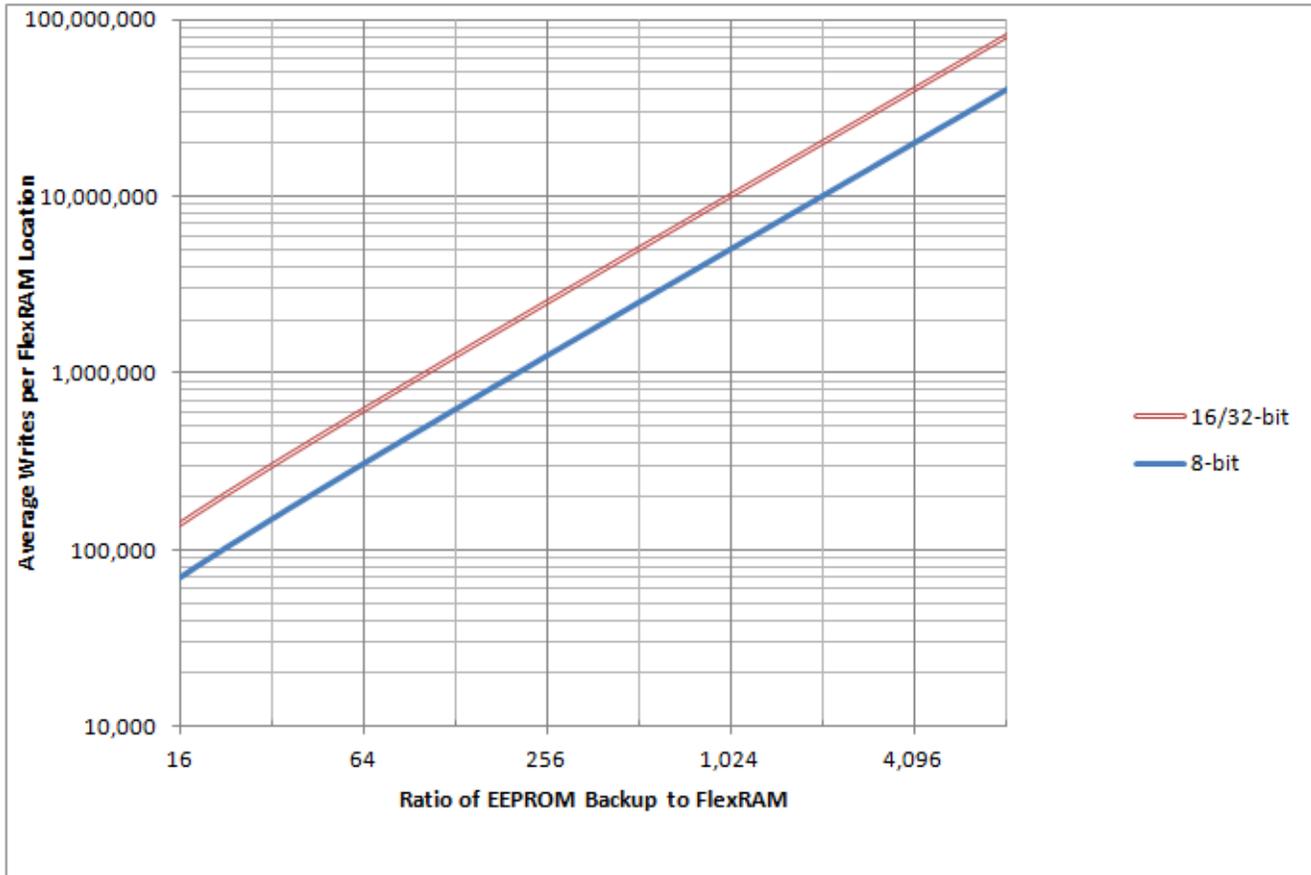


Figure 11. EEPROM backup writes to FlexRAM

3.4.2 EzPort switching specifications

Table 24. EzPort switching specifications

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
EP1	EZP_CK frequency of operation (all commands except READ)	—	$f_{\text{SYS}}/2$	MHz
EP1a	EZP_CK frequency of operation (READ command)	—	$f_{\text{SYS}}/8$	MHz
EP2	$\overline{\text{EZP_CS}}$ negation to next $\overline{\text{EZP_CS}}$ assertion	$2 \times t_{\text{EZP_CK}}$	—	ns
EP3	EZP_CS input valid to EZP_CK high (setup)	5	—	ns
EP4	EZP_CK high to $\overline{\text{EZP_CS}}$ input invalid (hold)	5	—	ns
EP5	EZP_D input valid to EZP_CK high (setup)	2	—	ns
EP6	EZP_CK high to EZP_D input invalid (hold)	5	—	ns
EP7	EZP_CK low to EZP_Q output valid	—	18	ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0	—	ns
EP9	$\overline{\text{EZP_CS}}$ negation to EZP_Q tri-state	—	12	ns

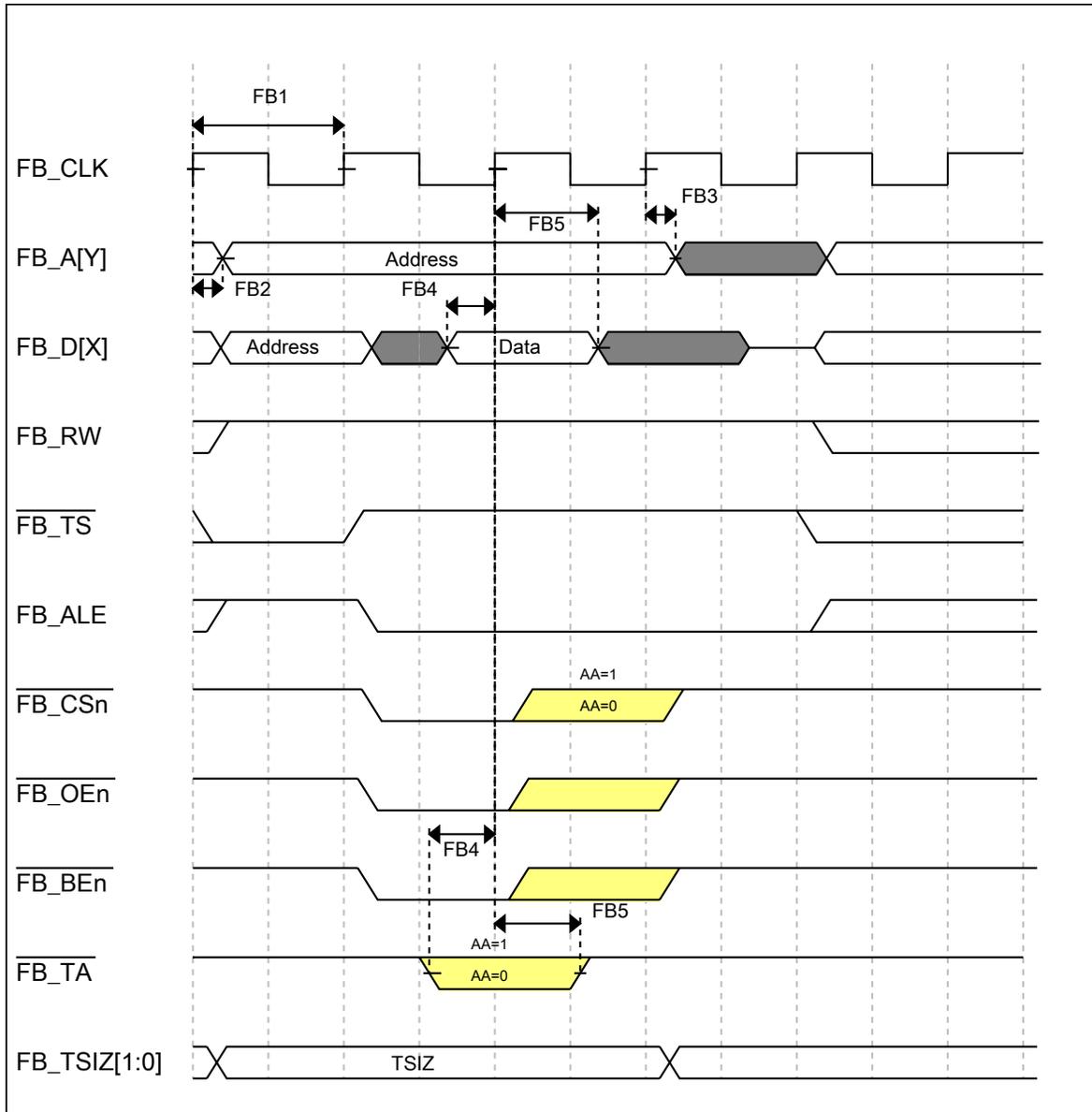


Figure 13. FlexBus read timing diagram

Table 28. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
E_{IL}	Input leakage error		$I_{in} \times R_{AS}$			mV	I_{in} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	8
V_{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	8

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume $V_{DDA} = 3.0$ V, Temp = 25 °C, $f_{ADCK} = 2.0$ MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
4. $1 \text{ LSB} = (V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.
8. ADC conversion clock < 3 MHz

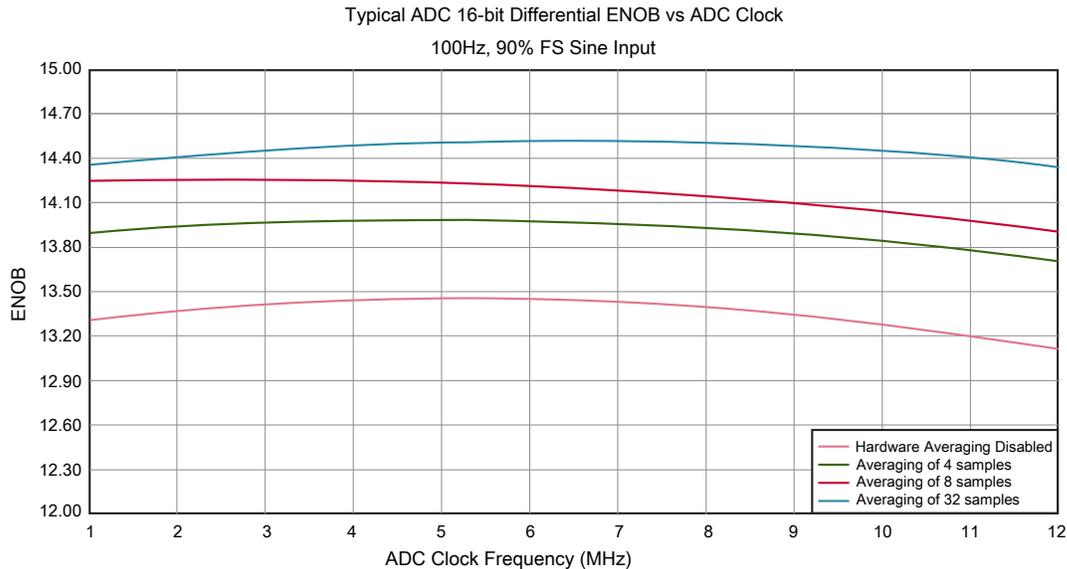


Figure 16. Typical ENOB vs. ADC_CLK for 16-bit differential mode

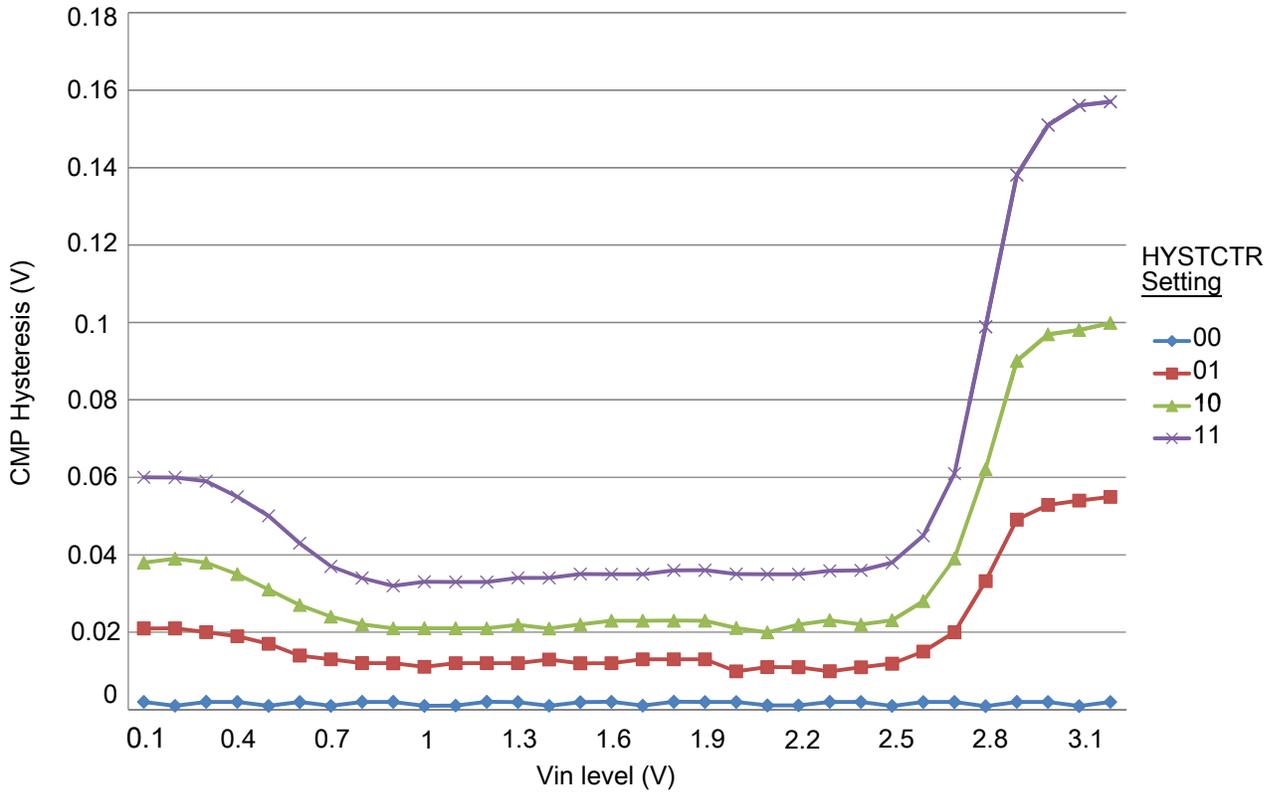


Figure 19. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

3.6.3 12-bit DAC electrical characteristics

3.6.3.1 12-bit DAC operating requirements

Table 30. 12-bit DAC operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V _{DDA}	Supply voltage	1.71	3.6	V	
V _{DACR}	Reference voltage	1.13	3.6	V	1
C _L	Output load capacitance	—	100	pF	2
I _L	Output load current	—	1	mA	

1. The DAC reference can be selected to be V_{DDA} or V_{REFH}.
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC.

3.6.3.2 12-bit DAC operating behaviors

Table 31. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	150	μA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	700	μA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	$V_{DACR} - 100$	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	± 8	LSB	2
DNL	Differential non-linearity error — $V_{DACR} > 2\text{ V}$	—	—	± 1	LSB	3
DNL	Differential non-linearity error — $V_{DACR} = V_{REF_OUT}$	—	—	± 1	LSB	4
V_{OFFSET}	Offset error	—	± 0.4	± 0.8	%FSR	5
E_G	Gain error	—	± 0.1	± 0.6	%FSR	5
PSRR	Power supply rejection ratio, $V_{DDA} \geq 2.4\text{ V}$	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	$\mu\text{V}/\text{C}$	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
A_C	Offset aging coefficient	—	—	100	$\mu\text{V}/\text{yr}$	
R_{op}	Output resistance (load = 3 k Ω)	—	—	250	Ω	
SR	Slew rate -80h → F7Fh → 80h <ul style="list-style-type: none"> • High power (SP_{HP}) • Low power (SP_{LP}) 	1.2 0.05	1.7 0.12	— —	$\text{V}/\mu\text{s}$	
CT	Channel to channel cross talk	—	—	-80	dB	
BW	3dB bandwidth <ul style="list-style-type: none"> • High power (SP_{HP}) • Low power (SP_{LP}) 	550 40	— —	— —	kHz	

1. Settling within ± 1 LSB
2. The INL is measured for 0 + 100 mV to $V_{DACR} - 100$ mV
3. The DNL is measured for 0 + 100 mV to $V_{DACR} - 100$ mV
4. The DNL is measured for 0 + 100 mV to $V_{DACR} - 100$ mV with $V_{DDA} > 2.4\text{ V}$
5. Calculated by a best fit curve from $V_{SS} + 100$ mV to $V_{DACR} - 100$ mV

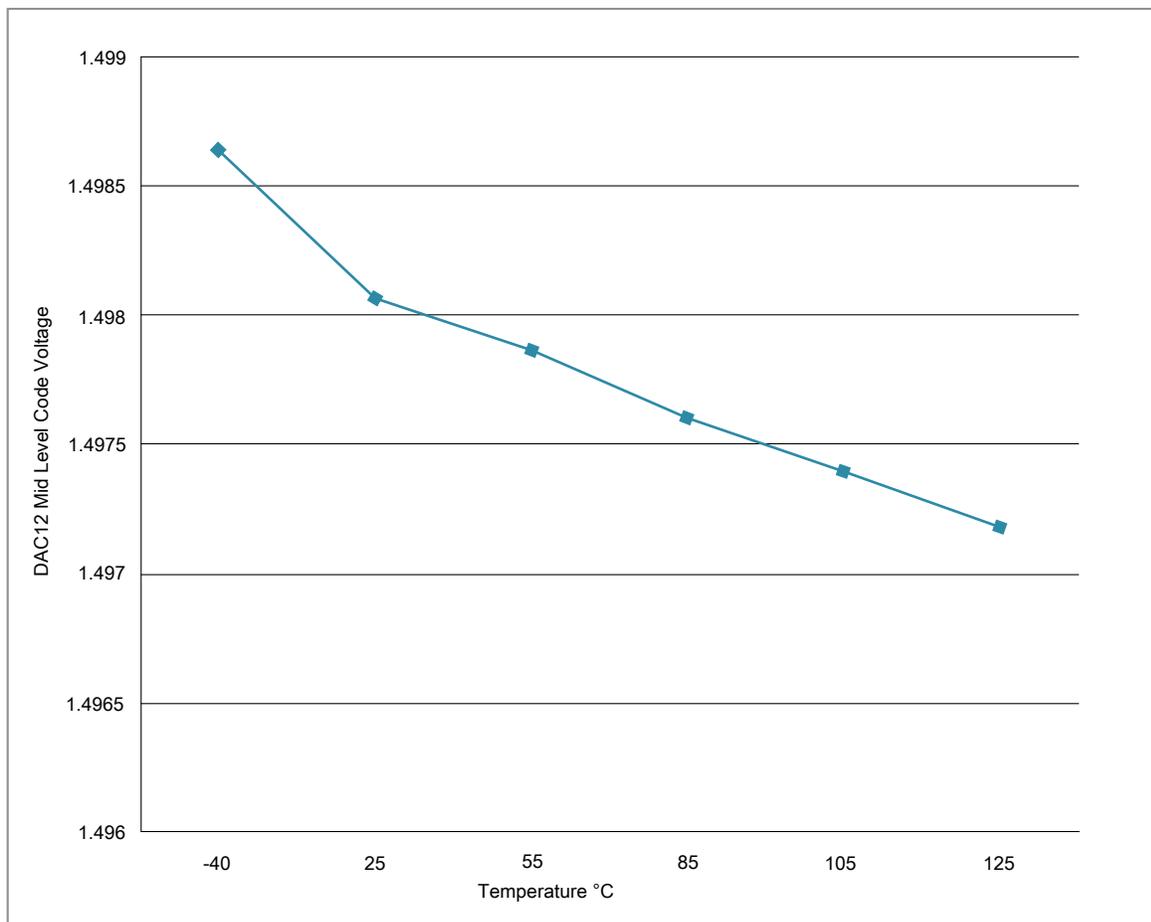


Figure 21. Offset at half scale vs. temperature

3.6.4 Voltage reference electrical specifications

Table 32. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	—
T_A	Temperature	Operating temperature range of the device		°C	—
C_L	Output load capacitance	100		nF	1, 2

1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
2. The load capacitance should not exceed +/-25% of the nominal specified C_L value over the operating temperature range of the device.

Table 33. VREF full-range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim at nominal V_{DDA} and temperature=25C	1.1915	1.195	1.1977	V	1
V_{out}	Voltage reference output — factory trim	1.1584	—	1.2376	V	1
V_{out}	Voltage reference output — user trim	1.193	—	1.197	V	1
V_{step}	Voltage reference trim step	—	0.5	—	mV	1
V_{tdrift}	Temperature drift (V_{max} - V_{min} across the full temperature range)	—	—	80	mV	1
I_{bg}	Bandgap only current	—	—	80	μ A	1
ΔV_{LOAD}	Load regulation • current = \pm 1.0 mA	—	200	—	μ V	1, 2
T_{stup}	Buffer startup time	—	—	100	μ s	—
V_{vdrift}	Voltage drift (V_{max} - V_{min} across the full voltage range)	—	2	—	mV	1

1. See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.
2. Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

Table 34. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_A	Temperature	0	50	$^{\circ}$ C	—

Table 35. VREF limited-range operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim	1.173	1.225	V	—

3.7 Timers

See [General switching specifications](#).

3.8 Communication interfaces

Table 37. USB VREG electrical specifications (continued)

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
	<ul style="list-style-type: none"> Run mode Standby mode 	2.1	2.8	3.6	V	
V _{Reg33out}	Regulator output voltage — Input supply (VREGIN) < 3.6 V, pass-through mode	2.1	—	3.6	V	2
C _{OUT}	External output capacitor	1.76	2.2	8.16	μF	
ESR	External output capacitor equivalent series resistance	1	—	100	mΩ	
I _{LIM}	Short circuit current	—	290	—	mA	

1. Typical values assume VREGIN = 5.0 V, Temp = 25 °C unless otherwise stated.
2. Operating in pass-through mode: regulator output voltage equal to the input voltage minus a drop proportional to I_{Load}.

3.8.4 CAN switching specifications

See [General switching specifications](#).

3.8.5 DSPI switching specifications (limited voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provide DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 38. Master mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	—	30	MHz	
DS1	DSPI_SCK output cycle time	2 × t _{BUS}	—	ns	
DS2	DSPI_SCK output high/low time	(t _{SCK} /2) – 2	(t _{SCK} /2) + 2	ns	
DS3	DSPI_PCS _n valid to DSPI_SCK delay	(t _{BUS} × 2) – 2	—	ns	1
DS4	DSPI_SCK to DSPI_PCS _n invalid delay	(t _{BUS} × 2) – 2	—	ns	2
DS5	DSPI_SCK to DSPI_SOUT valid	—	8.5	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	–2	—	ns	

Table continues on the next page...

Peripheral operating requirements and behaviors

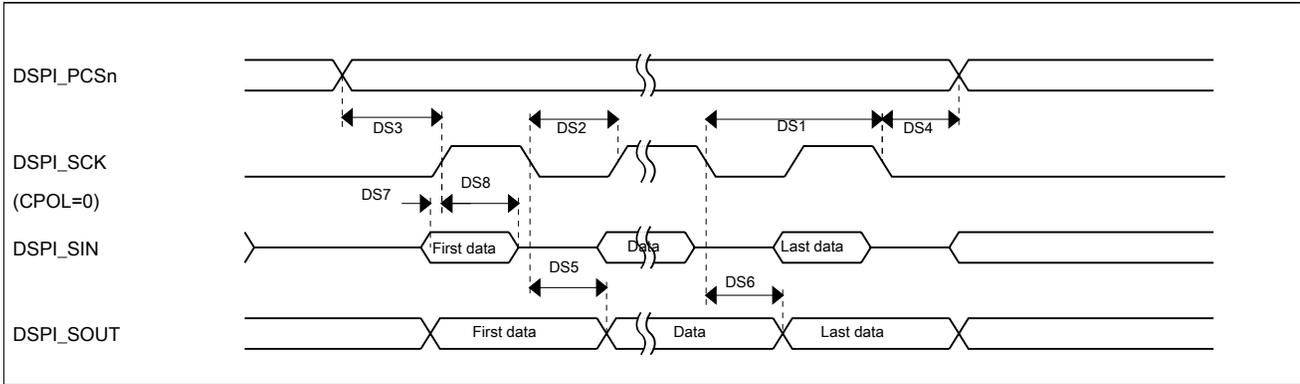


Figure 24. DSPI classic SPI timing — master mode

Table 41. Slave mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
	Frequency of operation	—	7.5	MHz
DS9	DSPI_SCK input cycle time	$8 \times t_{BUS}$	—	ns
DS10	DSPI_SCK input high/low time	$(t_{SCK}/2) - 4$	$(t_{SCK}/2) + 4$	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	20	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	DSPI_SS active to DSPI_SOUT driven	—	19	ns
DS16	DSPI_SS inactive to DSPI_SOUT not driven	—	19	ns

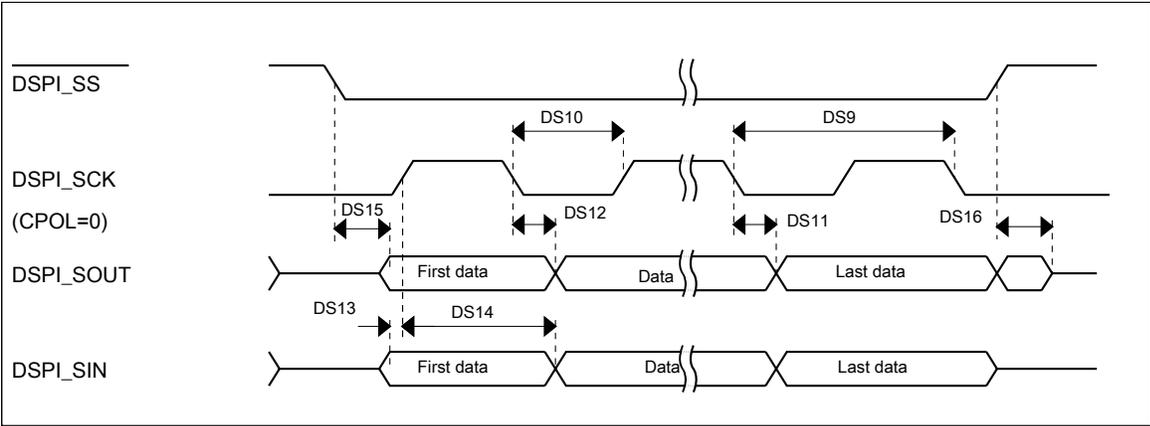


Figure 25. DSPI classic SPI timing — slave mode

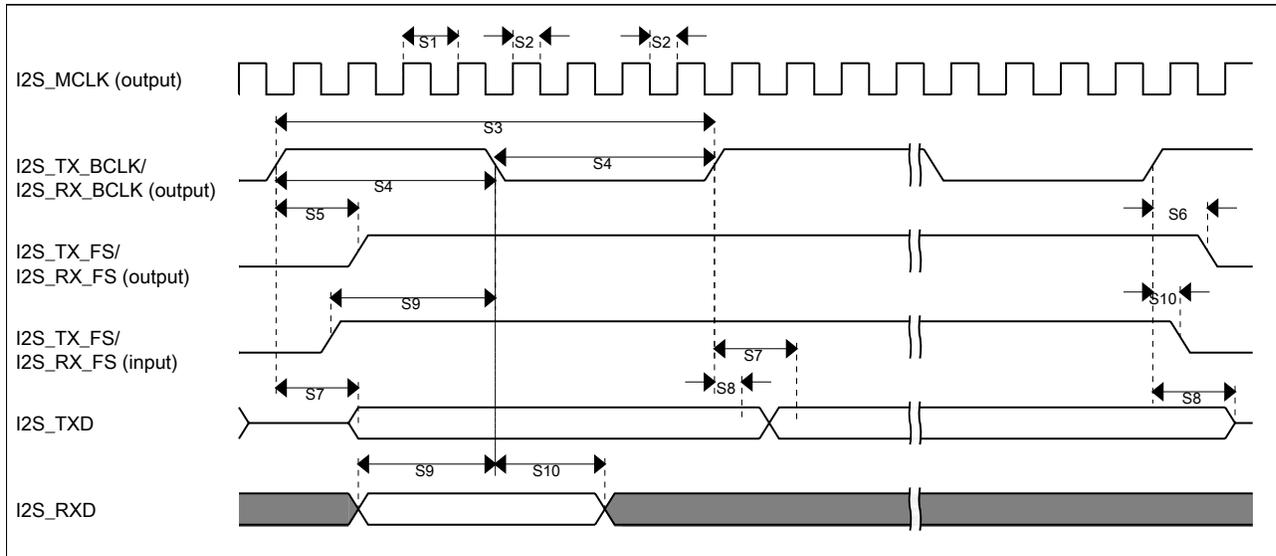


Figure 31. I2S/SAI timing — master modes

Table 48. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	250	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	30	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK		—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—		ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	30	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK		—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid ¹	—	72	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

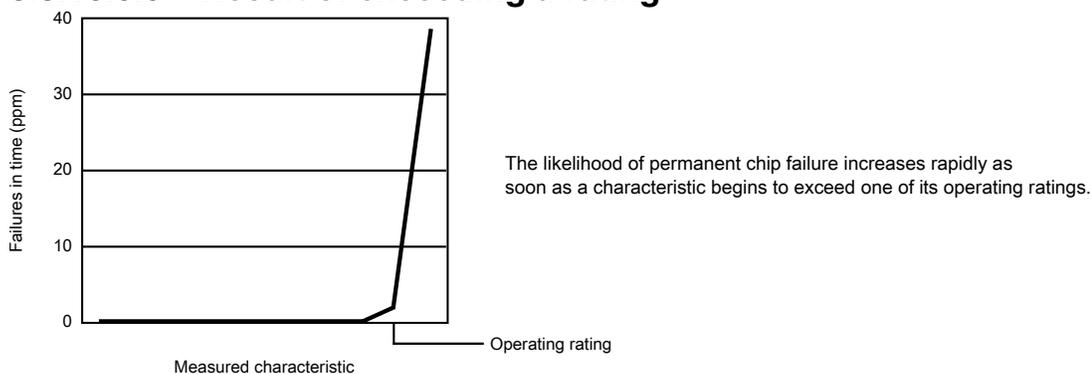
Peripheral operating requirements and behaviors

3.8.10.5.4.1 Example

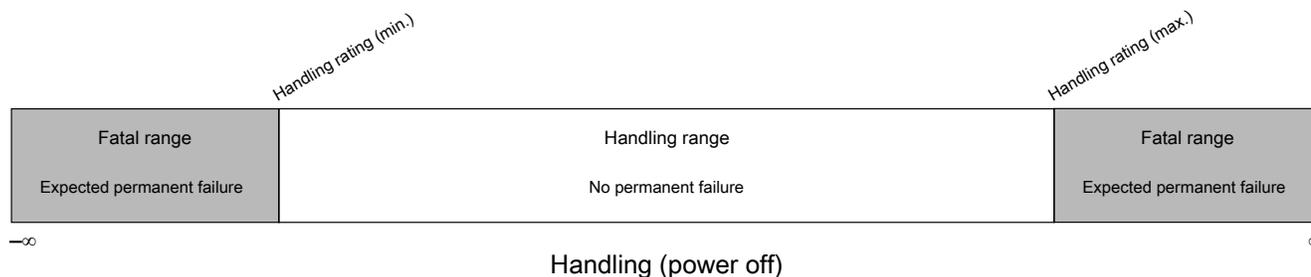
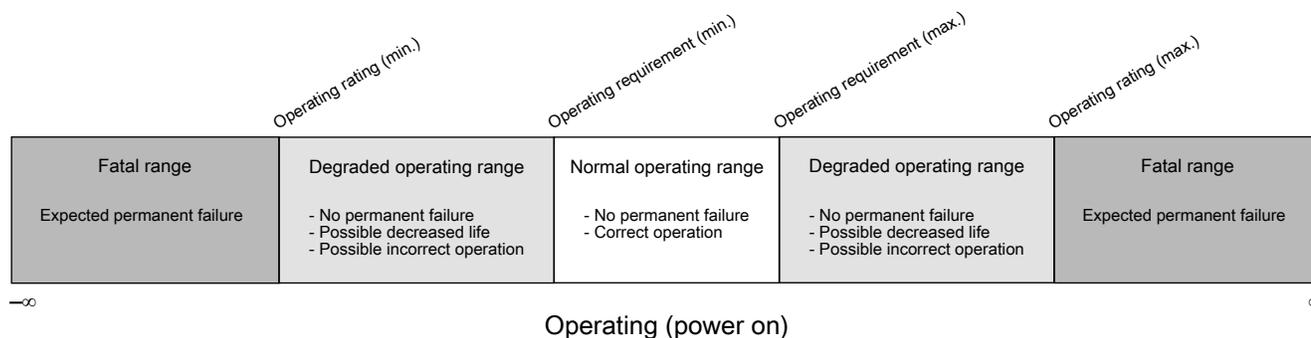
This is an example of an operating rating:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	-0.3	1.2	V

3.8.10.5.5 Result of exceeding a rating



3.8.10.5.6 Relationship between ratings and operating requirements



3.8.10.5.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

80 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
30	PTA4/ LLWU_P3	NMI_b/ EZP_CS_b		PTA4/ LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
31	PTA5	DISABLED		PTA5	USB_CLKIN	FTM0_CH2		CMP2_OUT	I2S0_TX_ BCLK	JTAG_TRST_ b	
32	PTA12	CMP2_IN0	CMP2_IN0	PTA12	CAN0_TX	FTM1_CH0		I2C2_SCL	I2S0_TXD0	FTM1_QD_ PHA	
33	PTA13/ LLWU_P4	CMP2_IN1	CMP2_IN1	PTA13/ LLWU_P4	CAN0_RX	FTM1_CH1		I2C2_SDA	I2S0_TX_FS	FTM1_QD_ PHB	
34	PTA14	DISABLED		PTA14	SPI0_PCS0	UART0_TX		I2C2_SCL	I2S0_RX_ BCLK	I2S0_TXD1	
35	PTA15	DISABLED		PTA15	SPI0_SCK	UART0_RX			I2S0_RXD0		
36	PTA16	DISABLED		PTA16	SPI0_SOUT	UART0_ CTS_b			I2S0_RX_FS	I2S0_RXD1	
37	PTA17	ADC1_SE17	ADC1_SE17	PTA17	SPI0_SIN	UART0_ RTS_b			I2S0_MCLK		
38	VDD	VDD	VDD								
39	VSS	VSS	VSS								
40	PTA18	EXTAL0	EXTAL0	PTA18		FTM0_FLT2	FTM_CLKIN0				
41	PTA19	XTAL0	XTAL0	PTA19		FTM1_FLT0	FTM_CLKIN1		LPTMR0_ ALT1		
42	RESET_b	RESET_b	RESET_b								
43	PTB0/ LLWU_P5	ADC0_SE8/ ADC1_SE8	ADC0_SE8/ ADC1_SE8	PTB0/ LLWU_P5	I2C0_SCL	FTM1_CH0			FTM1_QD_ PHA		
44	PTB1	ADC0_SE9/ ADC1_SE9	ADC0_SE9/ ADC1_SE9	PTB1	I2C0_SDA	FTM1_CH1			FTM1_QD_ PHB		
45	PTB2	ADC0_SE12	ADC0_SE12	PTB2	I2C0_SCL	UART0_ RTS_b			FTM0_FLT3		
46	PTB3	ADC0_SE13	ADC0_SE13	PTB3	I2C0_SDA	UART0_ CTS_b			FTM0_FLT0		
47	PTB10	ADC1_SE14	ADC1_SE14	PTB10	SPI1_PCS0	UART3_RX		FB_AD19	FTM0_FLT1		
48	PTB11	ADC1_SE15	ADC1_SE15	PTB11	SPI1_SCK	UART3_TX		FB_AD18	FTM0_FLT2		
49	VSS	VSS	VSS								
50	VDD	VDD	VDD								
51	PTB16	DISABLED		PTB16	SPI1_SOUT	UART0_RX	FTM_CLKIN0	FB_AD17	EWM_IN		
52	PTB17	DISABLED		PTB17	SPI1_SIN	UART0_TX	FTM_CLKIN1	FB_AD16	EWM_OUT_b		
53	PTB18	DISABLED		PTB18	CAN0_TX	FTM2_CH0	I2S0_TX_ BCLK	FB_AD15	FTM2_QD_ PHA		
54	PTB19	DISABLED		PTB19	CAN0_RX	FTM2_CH1	I2S0_TX_FS	FB_OE_b	FTM2_QD_ PHB		
55	PTC0	ADC0_SE14	ADC0_SE14	PTC0	SPI0_PCS4	PDB0_ EXTRG		FB_AD14	I2S0_TXD1		
56	PTC1/ LLWU_P6	ADC0_SE15	ADC0_SE15	PTC1/ LLWU_P6	SPI0_PCS3	UART1_ RTS_b	FTM0_CH0	FB_AD13	I2S0_TXD0		
57	PTC2	ADC0_SE4b/ CMP1_IN0	ADC0_SE4b/ CMP1_IN0	PTC2	SPI0_PCS2	UART1_ CTS_b	FTM0_CH1	FB_AD12	I2S0_TX_FS		